

Development of CPP devices : tunnel structures

(from February -> now)

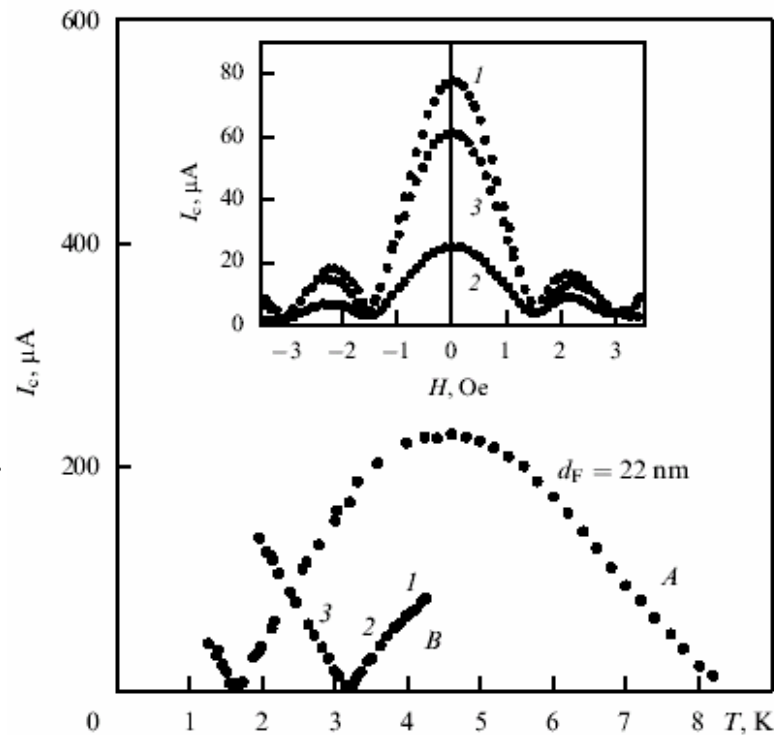
chris et al

Motivation

CPP junctions:

Josephson junctions with
F barriers: π -junctions

Crossover from 0 - π
state as a function of T



Ryazanov et al : S/F/S: Nb/CuNi/Nb, $50 \times 50 \mu\text{m}^2$ junctions

$R_N \sim 10^{-5} \Omega$ giving $I_C R_N \sim 1$ nV for sensible critical currents

Not easy to measure! (need SQUID picovoltmeter)

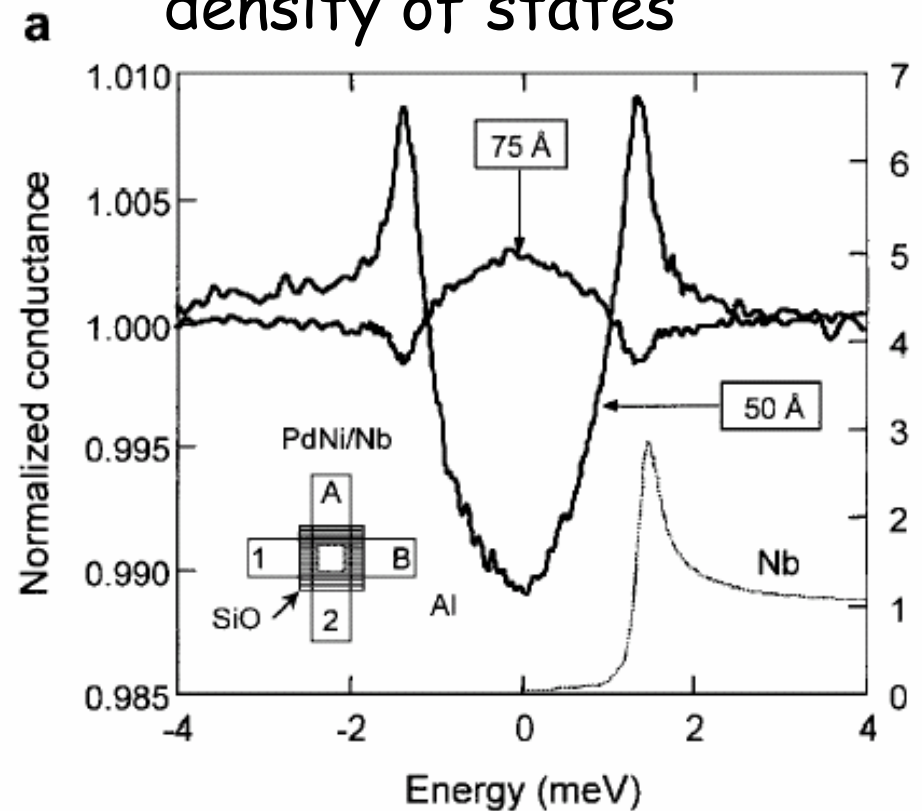
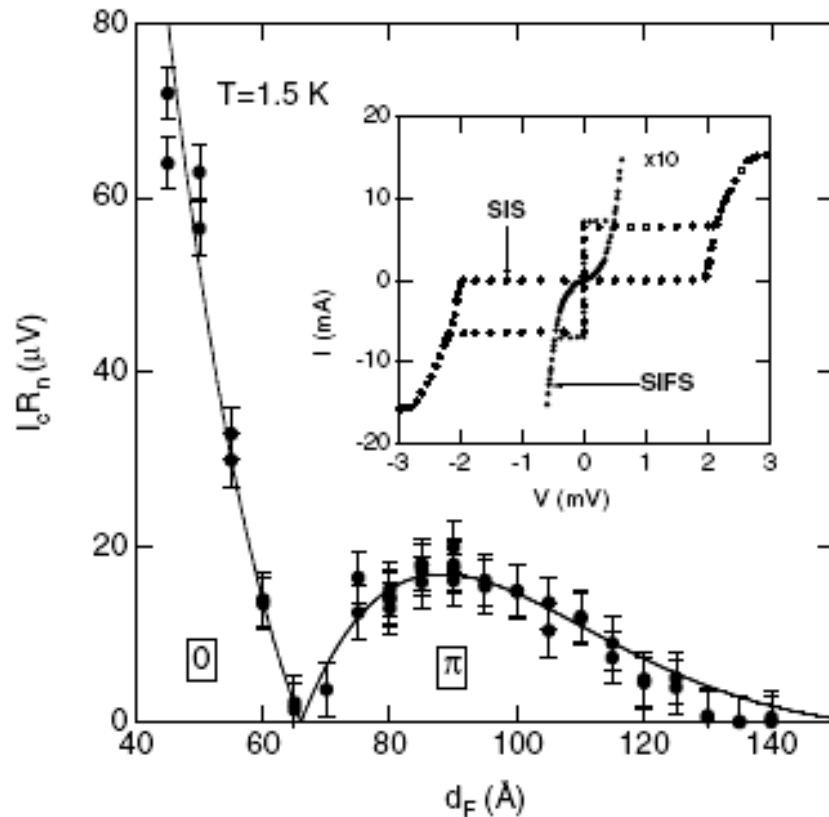
Motivation

Either: make the devices smaller to raise R_N , (and use thinner barriers to keep I_C high)

Or: add an I layer

ALSO: S/F/I/N

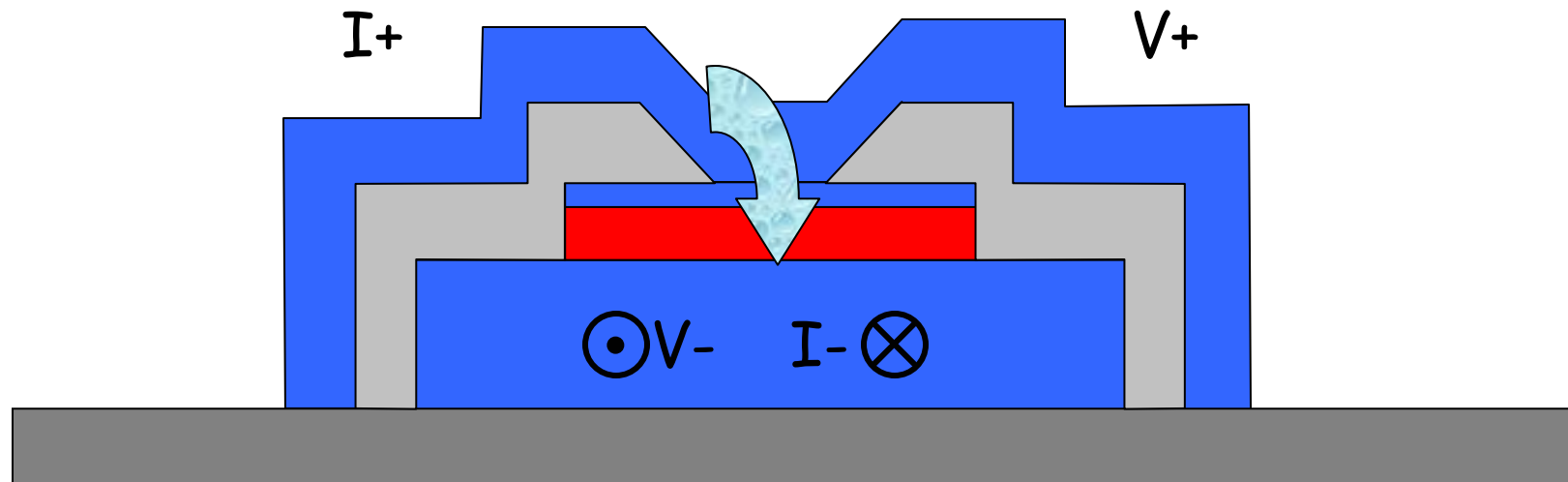
Now you measure the (inversion) of the density of states

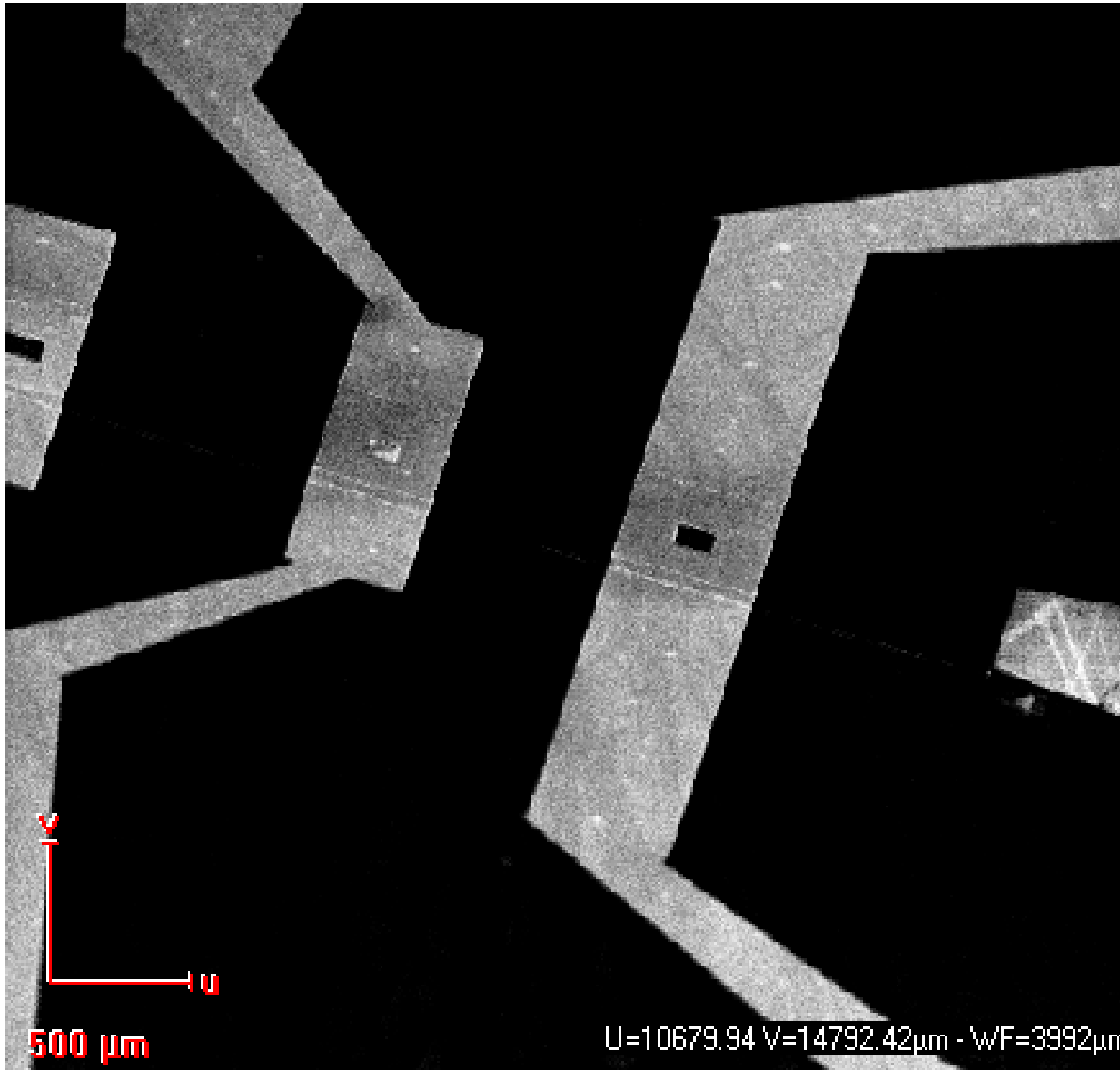


Nb/PdNi/ AlO_x /Nb junctions
 0 - π crossover vs F thickness

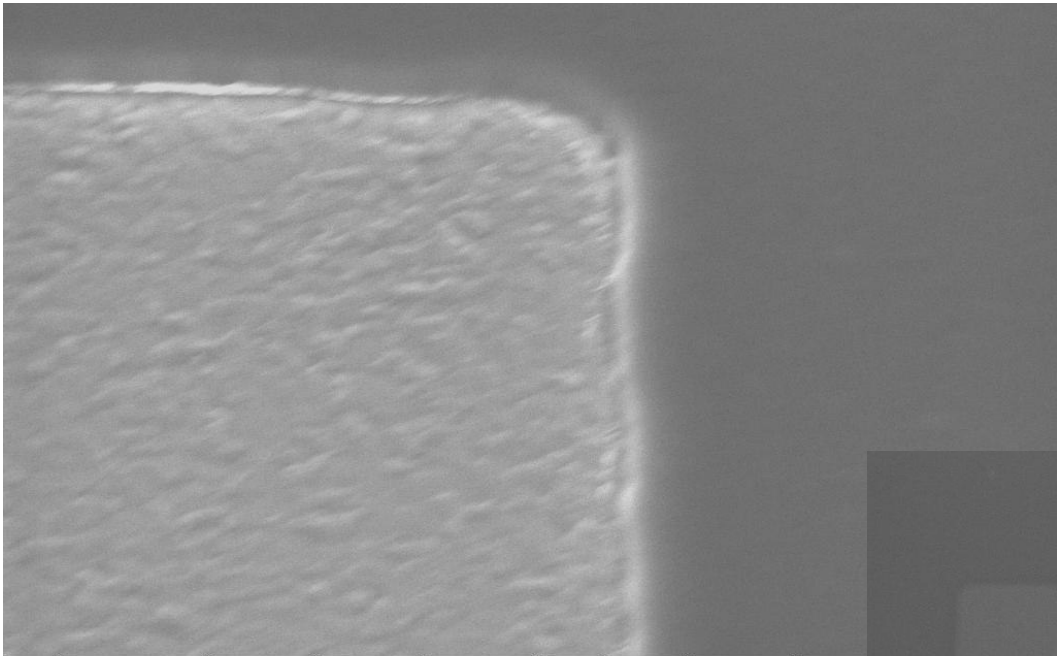
Kontos et al

Mesa structure





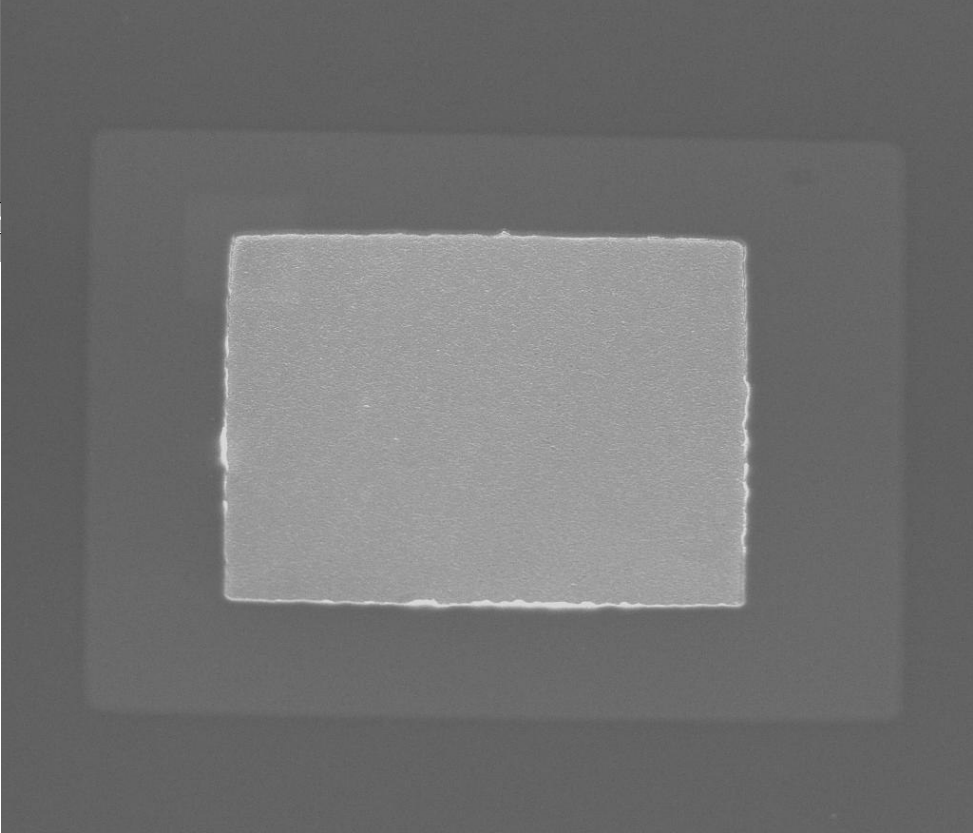
Charging means that the lift-off of the SiO layer was not done properly: PMMA Remains above the mesa which means you can't make a good contact



	8/30/2005 4:51:59 PM	HV 5.00 kV	WD 5.0 mm	mag 40 000 x	det TLD	dwell 24 μ s	HFW 3.73 μ m	
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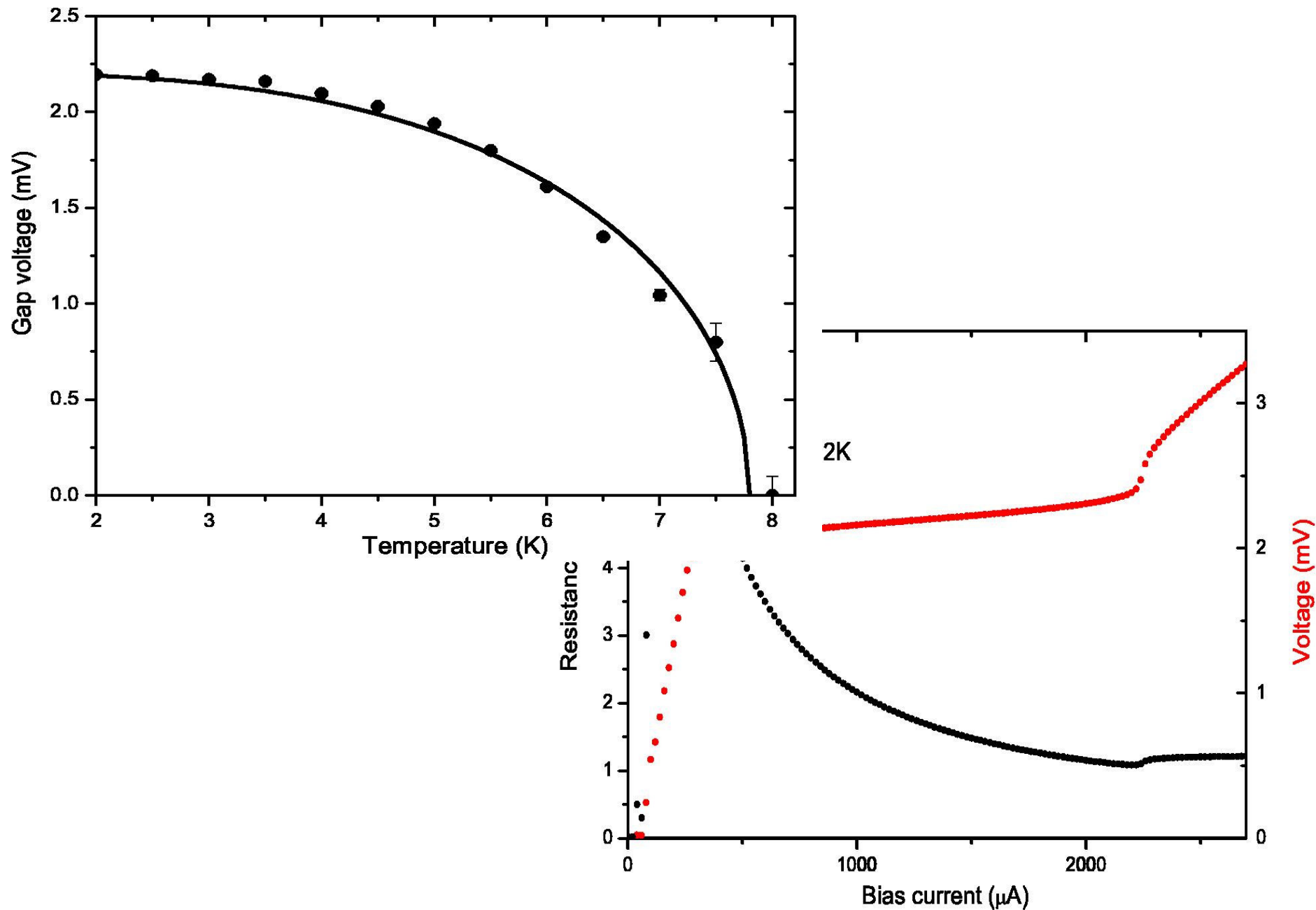
Better this time after ultrasounding thoroughly.

Left image tilted: no ears: smooth slope from SiO to Nb

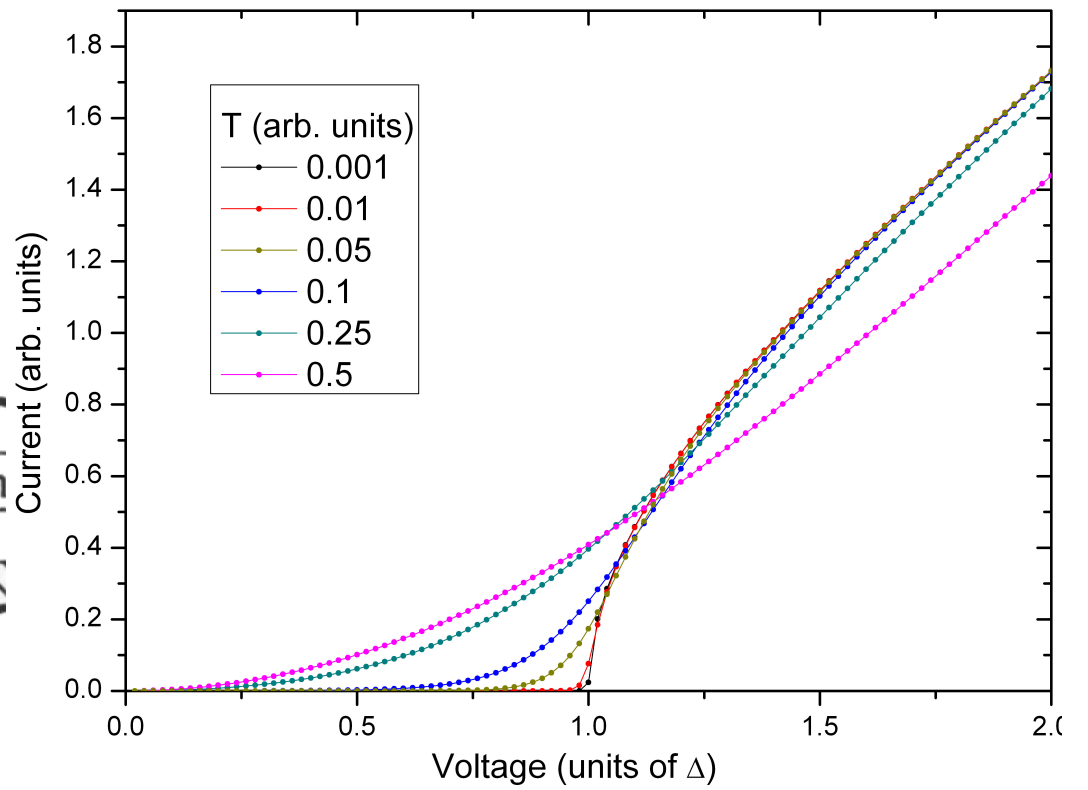
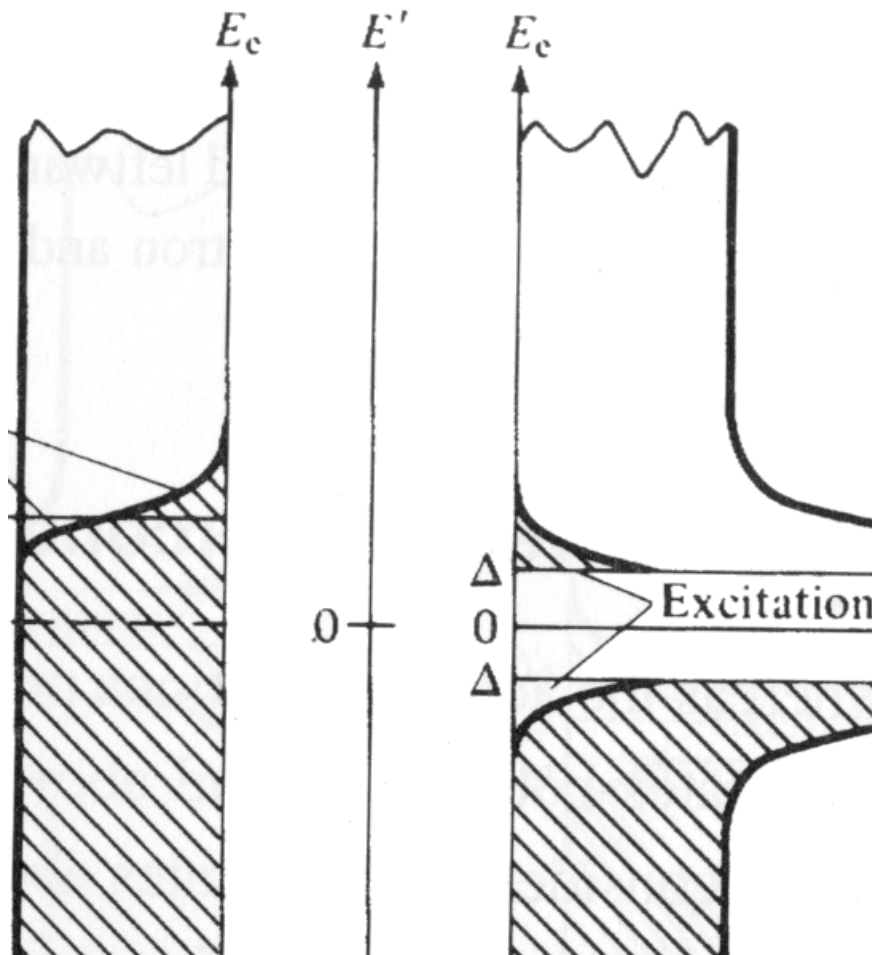


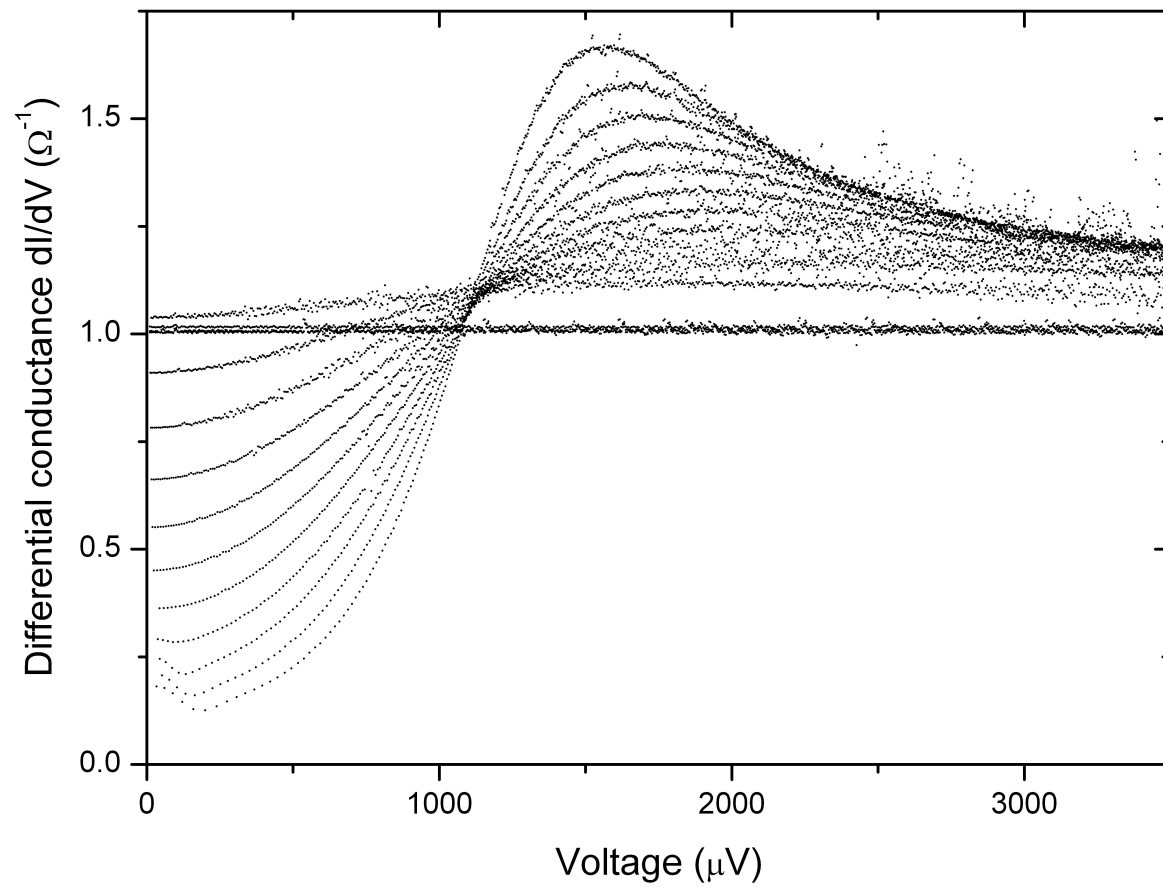
	8/30/2005 4:48:05 PM	HV 5.00 kV	WD 5.0 mm	mag 5 000 x	det TLD	dwell 24 μ s	HFW 29.8 μ m	 5 μ m
								NPE8

First tests : S/I/S

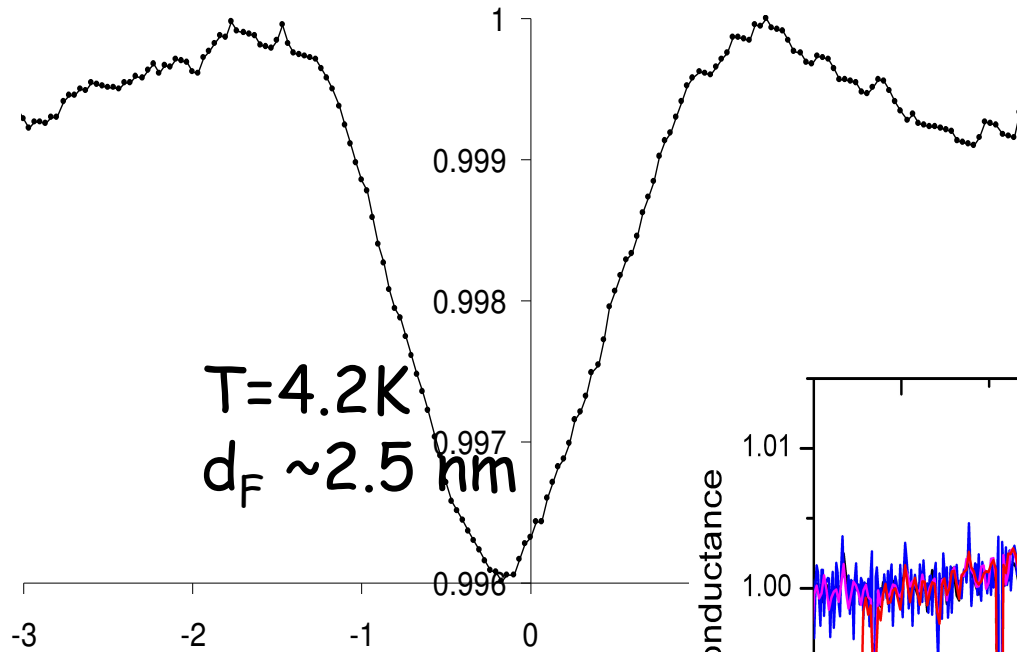


S/I/N

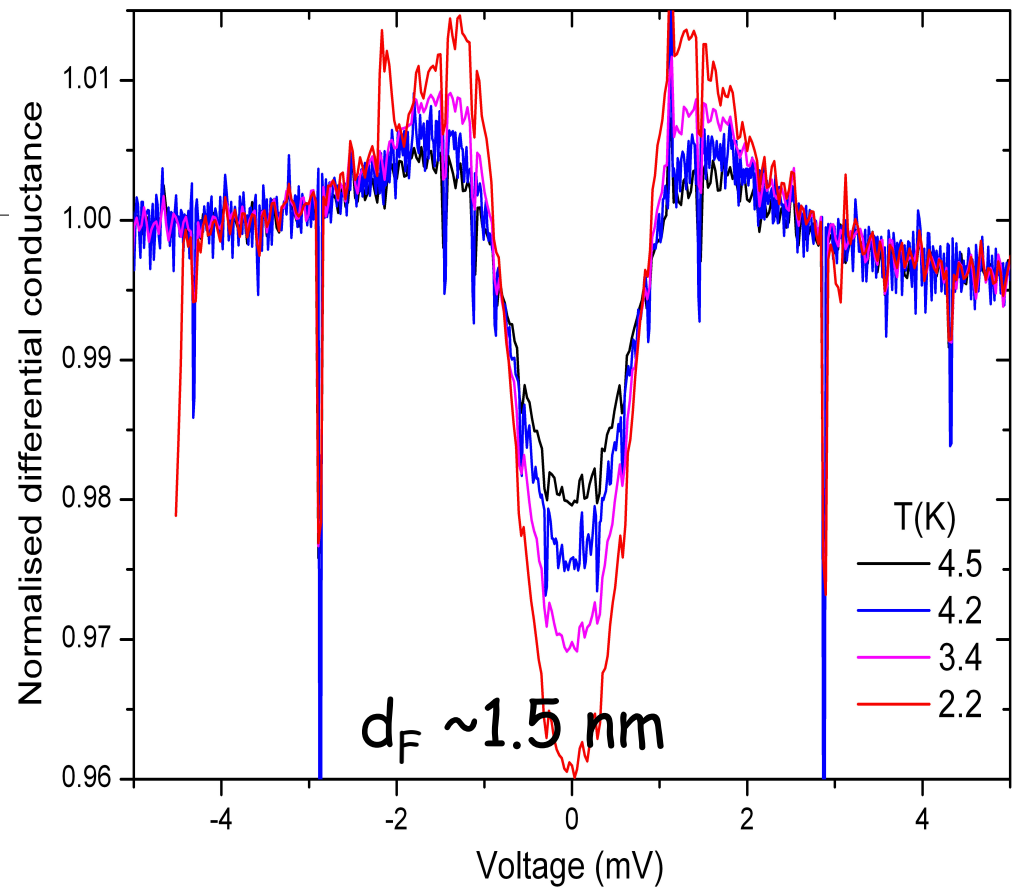


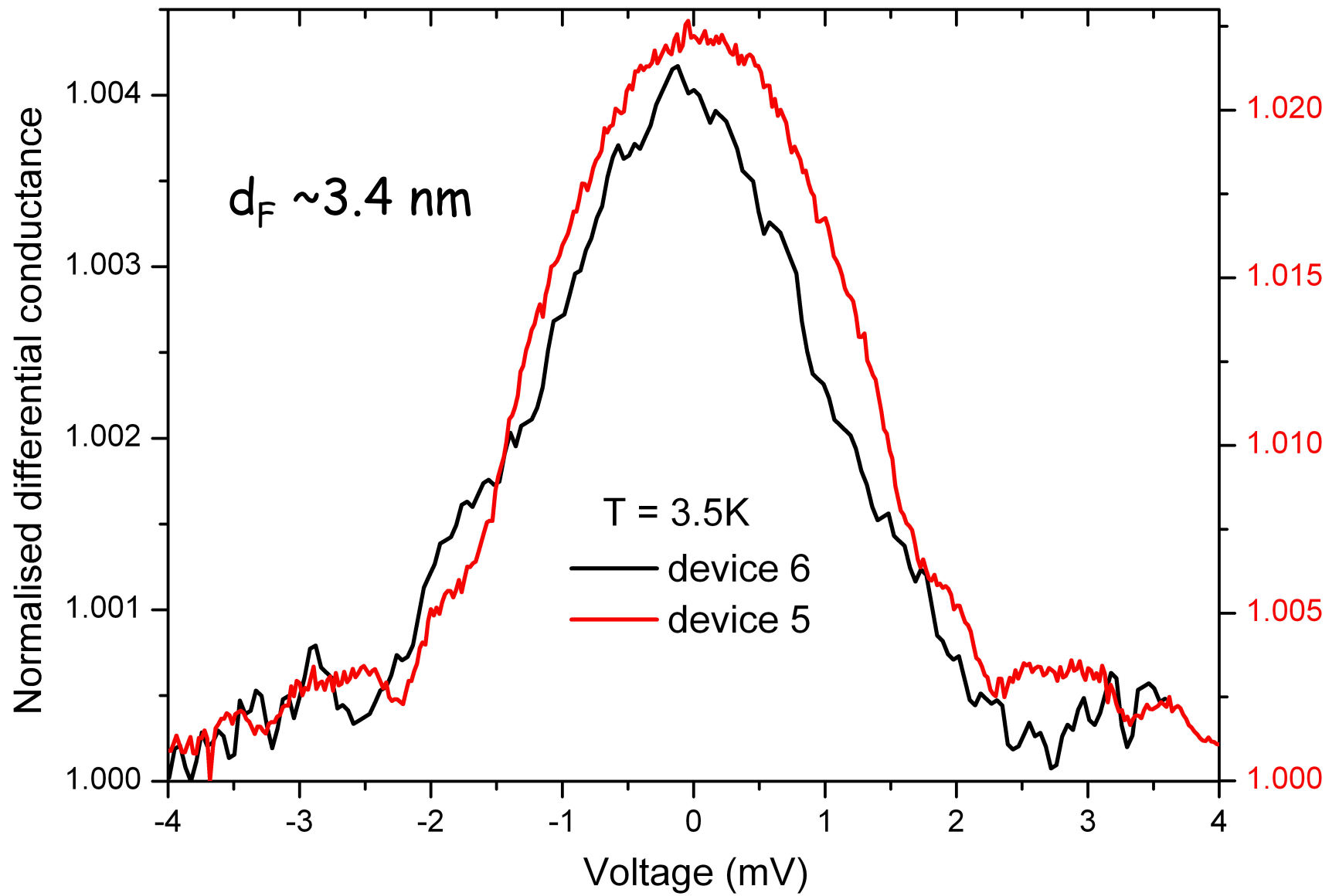


S/F/I/N



Signals very small, so need a lockin amplifier to measure diff. resistance directly (top)





Same chip – big difference in size of conductance change.
Is the inverted DoS real??

Future: experiments

- Get better processing!!
- For thickness with $N(0) \sim 0$ see if we can see $0-\pi$ crossover with T
- Try same things with Py instead of PdNi (show that strong F can make π junctions, and see what happens with domains: field tune a crossover??) & Josephson junctions
- Replace everything by amorphous things: MoGe / GdNi
- Follow up with STM if possible